

A Yu Kuznetsov

List of Publications by Year in descending order

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196
papers

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109321

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198
all docs

198
docs citations

198
times ranked

5348
citing authors

#	ARTICLE	IF	CITATIONS
1	Identification of oxygen and zinc vacancy optical signals in ZnO. Applied Physics Letters, 2006, 89, 262112.	3.3	387
2	Oxygen vacancies: The origin of n -type conductivity in ZnO. Physical Review B, 2016, 93, .	3.2	244
3	Controlled Growth of High-Quality ZnO-Based Films and Fabrication of Visible-Blind and Solar-Blind Ultra-Violet Detectors. Advanced Materials, 2009, 21, 4625-4630.	21.0	239
4	Iron and intrinsic deep level states in Ga ₂ O ₃ . Applied Physics Letters, 2018, 112, .	3.3	196
5	Impact of proton irradiation on conductivity and deep level defects in $\hat{\Gamma}^2$ -Ga ₂ O ₃ . APL Materials, 2019, 7, .	5.1	143
6	Zinc vacancy and oxygen interstitial in ZnO revealed by sequential annealing and electron irradiation. Physical Review B, 2012, 86, .	3.2	139
7	Nanostructure Formation and Passivation of Large-Area Black Silicon for Solar Cell Applications. Small, 2012, 8, 1392-1397.	10.0	137
8	Temperature dependence and decay times of zinc and oxygen vacancy related photoluminescence bands in zinc oxide. Solid State Communications, 2008, 145, 321-326.	1.9	121
9	Vacancy defect and defect cluster energetics in ion-implanted ZnO. Physical Review B, 2010, 81, .	3.2	121
10	Probing Defects in Nitrogen-Doped Cu ₂ O. Scientific Reports, 2014, 4, 7240.	3.3	96
11	Maskless inverted pyramid texturization of silicon. Scientific Reports, 2015, 5, 10843.	3.3	87
12	Back-illuminated Si photocathode: a combined experimental and theoretical study for photocatalytic hydrogen evolution. Energy and Environmental Science, 2015, 8, 650-660.	30.8	76
13	18.87%-efficient inverted pyramid structured silicon solar cell by one-step Cu-assisted texturization technique. Solar Energy Materials and Solar Cells, 2017, 166, 121-126.	6.2	76
14	Palladium Schottky barrier contacts to hydrothermally grown n-ZnO and shallow electron states. Applied Physics Letters, 2004, 85, 2259-2261.	3.3	75
15	Zinc oxide: bulk growth, role of hydrogen and Schottky diodes. Journal Physics D: Applied Physics, 2009, 42, 153001.	2.8	74
16	Single artificial atoms in silicon emitting at telecom wavelengths. Nature Electronics, 2020, 3, 738-743.	26.0	72
17	Deep level related photoluminescence in ZnMgO. Applied Physics Letters, 2010, 97, .	3.3	71
18	Vacancy clustering and acceptor activation in nitrogen-implanted ZnO. Physical Review B, 2008, 77, .	3.2	63

#	ARTICLE	IF	CITATIONS
19	Micro-structured inverted pyramid texturization of Si inspired by self-assembled Cu nanoparticles. <i>Nanoscale</i> , 2017, 9, 907-914.	5.6	59
20	Identification of substitutional Li in ZnO -type ZnO and its role as an acceptor. <i>Physical Review B</i> , 2011, 83, .	3.2	54
21	Deactivation of Li by vacancy clusters in ion-implanted and flash-annealed ZnO. <i>Physical Review B</i> , 2006, 74, .	3.2	52
22	Understanding phase separation in ZnCdO by a combination of structural and optical analysis. <i>Physical Review B</i> , 2011, 83, .	3.2	52
23	Nickel atomic diffusion in amorphous silicon. <i>Applied Physics Letters</i> , 1995, 66, 2229-2231.	3.3	49
24	Optical properties of an ensemble of G-centers in silicon. <i>Physical Review B</i> , 2018, 97, .	3.2	49
25	Broad Diversity of Near-Infrared Single-Photon Emitters in Silicon. <i>Physical Review Letters</i> , 2021, 126, 083602.	7.8	48
26	Phosphorus and boron diffusion in silicon under equilibrium conditions. <i>Applied Physics Letters</i> , 2003, 82, 2254-2256.	3.3	47
27	Dynamic annealing in ion implanted SiC: Flux versus temperature dependence. <i>Journal of Applied Physics</i> , 2003, 94, 7112-7115.	2.5	44
28	Influence of graphene synthesizing techniques on the photocatalytic performance of graphene-TiO ₂ nanocomposites. <i>Physical Chemistry Chemical Physics</i> , 2013, 15, 15528-15537.	2.8	43
29	Prediction of high efficiency ZnMgO/Si solar cells suppressing carrier recombination by conduction band engineering. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2013, 210, 585-588.	1.8	43
30	Effect of implanted species on thermal evolution of ion-induced defects in ZnO. <i>Journal of Applied Physics</i> , 2014, 115, .	2.5	43
31	Vacancy-phosphorus complexes in strained Si _{1-x} Ge _x : Structure and stability. <i>Physical Review B</i> , 2003, 68, .	3.2	42
32	Deuterium diffusion and trapping in hydrothermally grown single crystalline ZnO. <i>Applied Physics Letters</i> , 2008, 93, .	3.3	42
33	Ion mass effect on vacancy-related deep levels in Si induced by ion implantation. <i>Physical Review B</i> , 2002, 65, .	3.2	40
34	Engineering of optically defect free Cu ₂ O enabling exciton luminescence at room temperature. <i>Optical Materials Express</i> , 2013, 3, 2072.	3.0	38
35	Disorder-Induced Ordering in Gallium Oxide Polymorphs. <i>Physical Review Letters</i> , 2022, 128, 015704.	7.8	36
36	Structural and optical properties of ZnO _{0.1} Mg _{0.9} O multiple quantum wells grown on ZnO substrates. <i>Applied Physics Letters</i> , 2007, 90, 211909.	3.3	35

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37	Interface Engineering of High Efficiency Organic-Silicon Heterojunction Solar Cells. ACS Applied Materials & Interfaces, 2016, 8, 26-30.	8.0	35
38	Recent advancements in the development of radiation hard semiconductor detectors for S-LHC. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 2005, 552, 7-19.	1.6	33
39	Thermal process dependence of Li configuration and electrical properties of Li-doped ZnO. Applied Physics Letters, 2012, 100, 042107.	3.3	33
40	Solid-state photoelectrochemical H ₂ generation with gaseous reactants. Electrochimica Acta, 2013, 97, 320-325.	5.2	32
41	Diffusion of phosphorus in relaxed Si _{1-x} Ge _x films and strained Si/Si _{1-x} Ge _x heterostructures. Journal of Applied Physics, 2003, 94, 6533-6540.	2.5	30
42	Optical activity and defect/dopant evolution in ZnO implanted with Er. Journal of Applied Physics, 2015, 118, .	2.5	30
43	Development of radiation tolerant semiconductor detectors for the Super-LHC. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 2005, 546, 99-107.	1.6	29
44	Hydrogen implantation into ZnO for n ⁺ -layer formation. Applied Physics Letters, 2005, 87, 191910.	3.3	28
45	Defect evolution and impurity migration in Na-implanted ZnO. Physical Review B, 2011, 84, .	3.2	28
46	Intrinsic Point-Defect Balance in Self-Ion-Implanted ZnO. Physical Review Letters, 2013, 110, 015501.	7.8	28
47	Impact of chloride surface treatment on nano-porous GaN structure for enhanced water-splitting efficiency. Applied Surface Science, 2020, 532, 147465.	6.1	28
48	Bulk $\text{Ga}_{2}\text{O}_{3}$ with (010) and (201) Surface Orientation: Schottky Contacts and Point Defects. Materials Science Forum, 0, 897, 755-758.	0.3	27
49	Divacancy annealing in Si: Influence of hydrogen. Physical Review B, 2004, 69, .	3.2	26
50	Fluence, flux, and implantation temperature dependence of ion-implantation-induced defect production in ${}^{4}\text{H}\alpha\text{SiC}$. Journal of Applied Physics, 2005, 97, 033513.	2.5	26
51	Tuning light absorption by band gap engineering in ZnCdO as a function of MOVPE-synthesis conditions and annealing. Journal of Crystal Growth, 2011, 315, 301-304.	1.5	25
52	On the mechanism of enhanced photocatalytic activity of composite TiO ₂ /carbon nanofilms. Applied Catalysis B: Environmental, 2011, 106, 337-342.	20.2	24
53	Crucial role of implanted atoms on dynamic defect annealing in ZnO. Applied Physics Letters, 2014, 104, .	3.3	24
54	Doping of Silicon Carbide by Ion Implantation. Materials Science Forum, 2001, 353-356, 549-554.	0.3	23

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55	Diffusion and configuration of Li in ZnO. Journal of Applied Physics, 2013, 113, 023702.	2.5	23
56	Radiation Silicon Carbide Detectors Based on Ion Implantation of Boron. IEEE Transactions on Nuclear Science, 2014, 61, 2105-2111.	2.0	23
57	Vacancy and interstitial depth profiles in ion-implanted silicon. Journal of Applied Physics, 2003, 93, 871-877.	2.5	22
58	Sb lattice diffusion in Si _{1-x} Ge _x /Si(001) heterostructures: Chemical and stress effects. Physical Review B, 2004, 69, .	3.2	22
59	H passivation of Li on Zn-site in ZnO: Positron annihilation spectroscopy and secondary ion mass spectrometry. Physical Review B, 2011, 84, .	3.2	22
60	Sb-enhanced diffusion in strained Si _{1-x} Ge _x : Dependence on biaxial compression. Physical Review B, 1999, 59, 7274-7277.	3.2	21
61	Vacancy-related deep levels in n-type Si _{1-x} Ge _x strained layers. Physical Review B, 2001, 63, .	3.2	21
62	Formation and origin of the dominating electron trap in irradiated $\langle \text{mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline" \rangle \langle \text{mml:mi} \rangle \text{p} \langle \text{mml:mi} \rangle \langle \text{mml:math} \rangle$ -type silicon. Physical Review B, 2008, 78, .	3.2	20
63	Band gap maps beyond the delocalization limit: correlation between optical band gaps and plasmon energies at the nanoscale. Scientific Reports, 2018, 8, 848.	3.3	20
64	Sb-related defects in Sb-doped ZnO thin film grown by pulsed laser deposition. Journal of Applied Physics, 2018, 123, .	2.5	19
65	Channeling implantations of Al ⁺ into 6H silicon carbide. Applied Physics Letters, 1999, 74, 3990-3992.	3.3	18
66	Recombination centers in as-grown and electron-irradiated ZnO substrates. Journal of Applied Physics, 2007, 102, 093504.	2.5	18
67	Ge redistribution in SiO ₂ /SiGe structures under thermal oxidation: Dynamics and predictions. Journal of Applied Physics, 2012, 111, .	2.5	18
68	Channeled Implants in 6H Silicon Carbide. Materials Science Forum, 2000, 338-342, 889-892.	0.3	17
69	Structural and optical properties of polar and non-polar ZnO films grown by MOVPE. Journal of Crystal Growth, 2008, 310, 5020-5024.	1.5	17
70	Effect of spatial defect distribution on the electrical behavior of prominent vacancy point defects in swift-ion implanted Si. Physical Review B, 2009, 79, .	3.2	17
71	Interaction between Na and Li in ZnO. Applied Physics Letters, 2009, 95, 242111.	3.3	17
72	Effect of composition on damage accumulation in ternary ZnO-based oxides implanted with heavy ions. Journal of Applied Physics, 2010, 108, 033509.	2.5	17

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73	Cd diffusion and thermal stability of CdZnO/ZnO heterostructures. Applied Physics Letters, 2011, 99, .	3.3	17
74	Beryllium sites in MBE-grown BeZnO alloy films. Journal Physics D: Applied Physics, 2014, 47, 175102.	2.8	17
75	Self-diffusion measurements in isotopic heterostructures of undoped and in situ doped ZnO: Zinc vacancy energetics. Physical Review B, 2016, 94, .	3.2	17
76	Radiation-induced defect accumulation and annealing in Si-implanted gallium oxide. Journal of Applied Physics, 2022, 131, .	2.5	17
77	Native point defects at ZnO surfaces, interfaces and bulk films. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 1566-1569.	0.8	16
78	Selective nano-emitter fabricated by silver assisted chemical etch-back for multicrystalline solar cells. RSC Advances, 2013, 3, 15483.	3.6	16
79	Enhancement-mode ZnO/Mg _{0.5} Zn _{0.5} O HFET on Si. Journal Physics D: Applied Physics, 2014, 47, 255101.	2.8	16
80	Germanium-based quantum emitters towards a time-reordering entanglement scheme with degenerate exciton and biexciton states. Physical Review B, 2015, 91, .	3.2	16
81	Fluorine doping: a feasible solution to enhancing the conductivity of high-resistance wide bandgap Mg _{0.51} Zn _{0.49} O active components. Scientific Reports, 2015, 5, 15516.	3.3	16
82	Nickel distribution in crystalline and amorphous silicon during solid phase epitaxy of amorphous silicon. Journal of Applied Physics, 1998, 84, 6644-6649.	2.5	15
83	Ion implantation in 4H- α -SiC. Nuclear Instruments & Methods in Physics Research B, 2008, 266, 1367-1372.	1.4	15
84	Alloy-fluctuation-induced exciton localization in high-Mg-content (0.27 \times 0.55) wurtzite Mg _x Zn _{1-x} O epilayers. Journal Physics D: Applied Physics, 2010, 43, 285402.	2.8	15
85	Impurity Sublattice Localization in ZnO Revealed by Li Marker Diffusion. Physical Review Letters, 2013, 110, 175503.	7.8	15
86	Nanoscale mapping of optical band gaps using monochromated electron energy loss spectroscopy. Nanotechnology, 2017, 28, 105703.	2.6	15
87	Dominating migration barrier for intrinsic defects in gallium oxide: Dose-rate effect measurements. Applied Physics Letters, 2021, 118, .	3.3	15
88	Comparative study of divacancy and E-center electronic levels in Si and strained Si _{0.87} Ge _{0.13} layers. Journal of Applied Physics, 2000, 87, 4629-4631.	2.5	14
89	Changing vacancy balance in ZnO by tuning synthesis between zinc/oxygen lean conditions. Journal of Applied Physics, 2010, 108, 046101.	2.5	14
90	Stabilization of Ge-rich defect complexes originating from $\langle \langle \mathbf{E} \rangle \rangle$ centers in $\langle \langle \mathbf{Si} \rangle \rangle$ Physical Review B, 2010, 81, .	3.2	14

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91	Ge concentrations in pile-up layers of sub-100-nm SiGe films for nano-structuring by thermal oxidation. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2012, 30, .	1.2	14
92	Impurity-limited lattice disorder recovery in ion-implanted ZnO. Applied Physics Letters, 2012, 101, .	3.3	14
93	Evidence of defect band mechanism responsible for band gap evolution in ZnO alloys. Physical Review B, 2019, 100, .	2.2	14
94	Efficient, recyclable, and affordable daylight induced Cu/Cu ₂ O/CuI photocatalyst via an inexpensive iodine sublimation process. Applied Surface Science, 2021, 537, 147007.	6.1	14
95	Damage Reduction in Channeled Ion Implanted 6H-SiC. Materials Science Forum, 2000, 338-342, 893-896.	0.3	13
96	Visualization of MeV ion impacts in Si using scanning capacitance microscopy. Physical Review B, 2006, 73, .	3.2	13
97	Annealing study of hydrothermally grown ZnO wafers. Physica Scripta, 2006, T126, 10-14.	2.5	13
98	Vacancy-impurity pairs in relaxed Si _{1-x} Ge _x layers studied by positron annihilation spectroscopy. Physical Review B, 2006, 73, .	3.2	13
99	Annealing of ion implanted CdZnO. Journal Physics D: Applied Physics, 2012, 45, 235304.	2.8	13
100	Generation and metastability of deep level states in $\hat{\Gamma}^2$ -Ga ₂ O ₃ exposed to reverse bias at elevated temperatures. Journal of Applied Physics, 2019, 125, 185706.	2.5	13
101	High electron mobility single-crystalline ZnSn ₂ on ZnO (0001) substrates. CrystEngComm, 2020, 22, 6268-6274.	2.6	13
102	Damage Evolution in Al-implanted 4H SiC. Materials Science Forum, 2000, 338-342, 869-872.	0.3	12
103	Determination of parameters for channeling of protons in SiC polytype crystals in the backscattering geometry. Nuclear Instruments & Methods in Physics Research B, 2001, 184, 319-326.	1.4	12
104	Vacancy-related defect distributions in 11B-, 14N-, and 27Al-implanted 4H-SiC: Role of channeling. Journal of Applied Physics, 2004, 95, 57-63.	2.5	12
105	Electronic structure of the phosphorus-vacancy complex in silicon: A resonant-bond model. Physical Review B, 2004, 70, .	3.2	12
106	Excess vacancies in high energy ion implanted SiGe. Journal of Applied Physics, 2007, 101, 033508.	2.5	12
107	Control of Li configuration and electrical properties of Li-doped ZnO. Journal Physics D: Applied Physics, 2012, 45, 375301.	2.8	12
108	Spatial distribution of cavities in silicon formed by ion implantation generated excess vacancies. Journal of Applied Physics, 2004, 95, 4738-4741.	2.5	11

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109	Ion Implantation Processing and Related Effects in SiC. Materials Science Forum, 2006, 527-529, 781-786.	0.3	11
110	Li and OH-Li Complexes in Hydrothermally Grown Single-Crystalline ZnO. Journal of Electronic Materials, 2011, 40, 429-432.	2.2	11
111	Testing ZnO based photoanodes for PEC applications. Energy Procedia, 2012, 22, 101-107.	1.8	11
112	Interplay of dopants and native point defects in ZnO. Physica Status Solidi (B): Basic Research, 2013, 250, 2110-2113.	1.5	11
113	Nano-structuring in SiGe by oxidation induced anisotropic Ge self-organization. Journal of Applied Physics, 2013, 113, 104310.	2.5	11
114	Strain Modulation of Si Vacancy Emission from SiC Micro- and Nanoparticles. Nano Letters, 2020, 20, 8689-8695.	9.1	11
115	Correlations of thermal properties with grain structure, morphology, and defect balance in nanoscale polycrystalline ZnO films. Applied Surface Science, 2021, 546, 149095.	6.1	11
116	Thermally induced surface instability in ion-implanted Mg x Zn $1-x$ films. Physical Review B, 2011, 84, .	3.2	10
117	Tunneling in ZnO/ZnCdO quantum wells towards next generation photovoltaic cells. Solar Energy, 2014, 106, 82-87.	6.1	10
118	Effects of temperature, triazole and hot-pressing on the performance of TiO ₂ photoanode in a solid-state photoelectrochemical cell. Electrochimica Acta, 2014, 115, 66-74.	5.2	10
119	4H-SiC Neutron Sensors Based on Ion Implanted ¹⁰ B Neutron Converter Layer. IEEE Transactions on Nuclear Science, 2016, 63, 1976-1980.	2.0	10
120	ZnSn ₂ in Real Space and k-space: Lattice Constants, Dislocation Density, and Optical Band Gap. Advanced Optical Materials, 2021, 9, 2100015.	7.3	10
121	Irradiation enhanced diffusion of boron in delta-doped silicon. Journal of Applied Physics, 2001, 89, 5400-5405.	2.5	9
122	Influence of boron on radiation enhanced diffusion of antimony in delta-doped silicon. Journal of Applied Physics, 2002, 91, 4073-4077.	2.5	9
123	Formation and stability of radiation defect complexes in Si and Si:Ge: Composition and pressure effects. Nuclear Instruments & Methods in Physics Research B, 2003, 202, 107-113.	1.4	9
124	Correlation between nitrogen and carbon incorporation into MOVPE ZnO at various oxidizing conditions. Microelectronics Journal, 2009, 40, 232-235.	2.0	9
125	Improvements in Realizing 4H-SiC Thermal Neutron Detectors. EPJ Web of Conferences, 2016, 106, 05004.	0.3	9
126	Schottky contacts to hydrogen doped ZnO. Physica Status Solidi (A) Applications and Materials Science, 2008, 205, 1998-2001.	1.8	8

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127	Surface/strain energy balance controlling preferred orientation in CdZnO films. Journal of Applied Physics, 2011, 110, .	2.5	8
128	Temperature dependence of Cu ₂ O orientations in the oxidation of Cu (111)/ZnO (0001) by oxygen plasma. Chinese Physics B, 2012, 21, 076401.	1.4	8
129	Surface localization of the Er-related optical active centers in Er doped zinc oxide films. Journal of Applied Physics, 2017, 121, .	2.5	8
130	Defect annealing kinetics in ZnO implanted with Zn substituting elements: Zn interstitials and Li redistribution. Journal of Applied Physics, 2019, 125, .	2.5	8
131	A comparative analysis of oxidation rates for thin films of SiGe versus Si. Physica Status Solidi (A) Applications and Materials Science, 2012, 209, 1934-1939.	1.8	7
132	Bulk Growth and Impurities. Semiconductors and Semimetals, 2013, 88, 67-104.	0.7	7
133	First tests of silicon-carbide semiconductors as candidate neutron detector for the ITER Test Blanket Modules. , 2013, , .		7
134	On the interplay of point defects and Cd in non-polar ZnCdO films. Journal of Applied Physics, 2013, 113, 023512.	2.5	7
135	Bandgap bowing in crystalline (ZnO) _{1-x} (GaN) _x thin films; influence of composition and structural properties. Semiconductor Science and Technology, 2019, 34, 015001.	2.0	7
136	Experimental exploration of the amphoteric defect model by cryogenic ion irradiation of a range of wide band gap oxide materials. Journal of Physics Condensed Matter, 2020, 32, 415704.	1.8	7
137	Formation of carbon interstitial-related defect levels by thermal injection of carbon into n-type 4H-SiC. Journal of Applied Physics, 2022, 131, .	2.5	7
138	Effect of injection of Si self-interstitials on Sb diffusion in Si/Si _{1-x} Gex/Si heterostructures. Physical Review B, 1998, 58, R13355-R13358.	3.2	6
139	An investigation of Fe-doped ZnO thin films grown by magnetron sputtering. Physica Scripta, 2010, T141, 014004.	2.5	6
140	Study of the Stability of 4H-SiC Detectors by Thermal Neutron Irradiation. Materials Science Forum, 0, 821-823, 875-878.	0.3	6
141	Limitation of Na-H codoping in achieving device-quality p-type ZnO. Materials Science in Semiconductor Processing, 2017, 69, 28-31.	4.0	6
142	GaZn-VZn acceptor complex defect in Ga-doped ZnO. Science China: Physics, Mechanics and Astronomy, 2018, 61, 1.	5.1	6
143	Activation energy of silicon diffusion in gallium oxide: Roles of the mediating defects charge states and phase modification. Applied Physics Letters, 2021, 119, .	3.3	6
144	Comparison of Strain Relaxation in Si/SiGe/Si Heterostructures after Annealing in Oxidizing and Inert Atmospheres. Physica Scripta, 1999, T79, 202.	2.5	5

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145	Phosphorus Diffusion in Si _{1-x} Ge _x , Defect and Diffusion Forum, 2001, 194-199, 709-716.	0.4	5
146	Influence of doping on thermal stability of Si/Si ^{1-x} Ge ^x /Si heterostructures. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2003, 102, 53-57.	3.5	5
147	Carrier concentration and shallow electron states in In-doped hydrothermally grown ZnO. Superlattices and Microstructures, 2005, 38, 364-368.	3.1	5
148	Hydrothermally Grown Single-Crystalline Zinc Oxide; Characterization and Modification. Materials Research Society Symposia Proceedings, 2007, 1035, 1.	0.1	5
149	Bandgap and band edge positions in compositionally graded ZnCdO. Journal of Applied Physics, 2018, 124, .	2.5	5
150	Acceptor complex signatures in oxygen-rich ZnO thin films implanted with chlorine ions. Journal of Applied Physics, 2020, 128, .	2.5	5
151	Effects of annealing on photoluminescence and defect interplay in ZnO bombarded by heavy ions: Crucial role of the ion dose. Journal of Applied Physics, 2020, 127, 025701.	2.5	5
152	Copper diffusion in amorphous germanium. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1998, 16, 2604-2607.	2.1	4
153	Diffusion of Phosphorus in Strained Si/SiGe/Si Heterostructures. Materials Research Society Symposia Proceedings, 1999, 568, 271.	0.1	4
154	Optical Investigation of the Built-In Strain in 3C-SiC Epilayers. Materials Science Forum, 2004, 457-460, 657-660.	0.3	4
155	Carrier concentration and shallow electron states in Sb-doped hydrothermally grown ZnO. Superlattices and Microstructures, 2007, 42, 294-298.	3.1	4
156	Common point defects in as-grown ZnO substrates studied by optical detection of magnetic resonance. Journal of Crystal Growth, 2008, 310, 1006-1009.	1.5	4
157	Engineering of nearly strain-free ZnO films on Si(111) by tuning AlN buffer thickness. Physica B: Condensed Matter, 2012, 407, 1476-1480.	2.7	4
158	Nuclear Radiation Detectors Based on 4H-SiC p ⁺ /n Junction. Materials Science Forum, 0, 778-780, 1046-1049.	0.3	4
159	Fermi level controlled point defect balance in ion irradiated indium oxide. Journal of Applied Physics, 2021, 130, 085703.	2.5	4
160	Impurity-assisted annealing of point defect complexes in ion-implanted silicon. Physica B: Condensed Matter, 1999, 273-274, 489-492.	2.7	3
161	Palladium Schottky barrier contacts to the (0001 _r)- and (101 _r ,0)-face of hydrothermally grown n-ZnO. AIP Conference Proceedings, 2005, , .	0.4	3
162	Millisecond processing beyond chip technology: From electronics to photonics. , 2007, , .		3

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163	Effect of growth temperature on the characteristics of ZnO films grown on Si(111) substrates by metal-organic chemical vapor deposition. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2008, 26, 224-227.	2.1	3
164	Carrier dynamics in linearly and step graded bandgap Zn _{1-x} Cd _x O structures. Applied Physics Letters, 2013, 102, .	3.3	3
165	Al incorporation during metal organic chemical vapour deposition of aluminium zinc oxide. Thin Solid Films, 2020, 709, 138245.	1.8	3
166	Carbon vacancy control in p ⁺ -n silicon carbide diodes for high voltage bipolar applications. Journal Physics D: Applied Physics, 2021, 54, 455106.	2.8	3
167	Structural Defects in Ion Implanted 4H-SiC Epilayers. Materials Research Society Symposia Proceedings, 2000, 640, 1.	0.1	2
168	Phosphorus diffusion in silicon; influence of annealing conditions. Materials Research Society Symposia Proceedings, 2001, 669, 1.	0.1	2
169	Vacancy-Type Defect Distributions of ¹¹ B-, ¹⁴ N- and ²⁷ Al-Implanted 4H-SiC Studied by Positron Annihilation Spectroscopy. Materials Science Forum, 2003, 433-436, 641-644.	0.3	2
170	Defect Behaviour in Deuterated and Non-Deuterated n-Type Si. Solid State Phenomena, 2005, 108-109, 553-560.	0.3	2
171	Anomalous Diffusion of Intrinsic Defects in K ⁺ Implanted ZnO using Li as Tracer. Materials Research Society Symposia Proceedings, 2012, 1394, 75.	0.1	2
172	Resolving Jahn-Teller induced vibronic fine structure of silicon vacancy quantum emission in silicon carbide. Physical Review B, 2021, 104, .	3.2	2
173	Characterization of Al-implanted 4H SiC High Voltage Diodes. Physica Scripta, 2002, T101, 207.	2.5	2
174	Photoluminescence intensity of Cu-doped ZnO modulated via defect occupancy by applying electric bias. Journal Physics D: Applied Physics, 2022, 55, 315102.	2.8	2
175	Thermal donor and antimony energy levels in relaxed Si _{1-x} Gex layers. Physical Review B, 2000, 61, 1708-1711.	3.2	1
176	Diffusion of Dopants and Impurities in Device Structures of SiC, SiGe and Si. Defect and Diffusion Forum, 2001, 194-199, 597-610.	0.4	1
177	Hydrogen Migration in Single Crystalline ZnO. Materials Research Society Symposia Proceedings, 2007, 1035, 1.	0.1	1
178	Scanning spreading resistance microscopy of defect engineered low dose SIMOX samples. Microelectronic Engineering, 2007, 84, 547-550.	2.4	1
179	High Zn Content Single-phase RS-MgZnO Suitable for Solar-blind Frequency Applications. , 2010, , .		1
180	Temperature dependence of surface plasmon mediated near band-edge emission from Ag/ZnO nanorods. Journal of Optics (United Kingdom), 2011, 13, 075003.	2.2	1

#	ARTICLE	IF	CITATIONS
181	Time-resolved spectroscopy of carrier dynamics in graded ZnCd _x O multilayer structures. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2012, 9, 1805-1808.	0.8	1
182	CdO/ZnO multiple quantum wells as components for next generation solar cells. , 2013, , .		1
183	4H-SiC neutron sensors based on ion implanted 10B neutron converter layer. , 2015, , .		1
184	Fine structure in electronic transitions attributed to nitrogen donor in silicon carbide. <i>Applied Physics Letters</i> , 2021, 119, 262101.	3.3	1
185	Activation Enthalpy of Sb Diffusion in Biaxially Compressed SiGe Layers. <i>Materials Research Society Symposia Proceedings</i> , 1998, 527, 435.	0.1	0
186	Channeling Measurements of Ion Implantation Damage in 4H-SiC. <i>Materials Science Forum</i> , 2001, 353-356, 595-598.	0.3	0
187	Implanted p+n-junctions in Silicon Carbide. <i>AIP Conference Proceedings</i> , 2003, , .	0.4	0
188	Capacitance spectroscopy study of InAs quantum dots and dislocations in p-GaAs matrix. <i>AIP Conference Proceedings</i> , 2005, , .	0.4	0
189	Scanning probe microscopy of single Au ion implants in Si. <i>Materials Science and Engineering C</i> , 2006, 26, 782-787.	7.3	0
190	Si-based Materials for Advanced Microelectronic Devices: Synthesis, Defects and Diffusion. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2006, 253, vii-viii.	1.4	0
191	Transportation of Na and Li in Hydrothermally Grown ZnO. <i>Materials Research Society Symposia Proceedings</i> , 2009, 1201, 1.	0.1	0
192	Reply to Comment on "Nanoscale mapping of optical band gaps using monochromated electron energy loss spectroscopy". <i>Nanotechnology</i> , 2018, 29, 318002.	2.6	0
193	Phase stability and strain accumulation in CdO as a function of Cd/O supply during MOVPE synthesis. <i>Superlattices and Microstructures</i> , 2018, 120, 569-577.	3.1	0
194	Energetics, migration and trapping of Zn interstitials in ZnO. <i>Journal Physics D: Applied Physics</i> , 2019, 52, 485103.	2.8	0
195	Studying Properties of Defects. , 2020, , 1-20.		0
196	Radiation and Emission in Materials: Similarity of Principles and Multi-Functional Applications. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2021, 218, 2000772.	1.8	0